











CSD17577Q5A

SLPS516-AUGUST 2014

CSD17577Q5A 30-V N-Channel NexFET™ Power MOSFET

Features

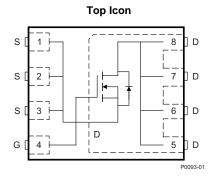
- Low Q_a and Q_{ad}
- Low Thermal Resistance
- Avalanche Rated
- Pb Free Terminal Plating
- **RoHS Compliant**
- Halogen Free
- SON 5 mm × 6 mm Plastic Package

2 Applications

- Point of Load Synchronous Buck in Networking, Telecom, and Computing Systems
- Optimized for Control, and Sync FET Applications

Description

This 30 V, 3.5 m Ω , SON 5 mm × 6 mm NexFETTM power MOSFET is designed to minimize resistance in power conversion applications.



$R_{DS(on)}$ vs V_{GS} 14 $T_C = 25^{\circ}C, I_D = 16A$ $R_{DS(on)}$ - On-State Resistance $\,(m\Omega)\,$ $T_C = 125^{\circ}C, I_D = 16A$ 12 10 8 6 2 0 0 10 12 V_{GS} - Gate-to- Source Voltage (V) G001

Product Summary

$T_A = 25^\circ$	С	TYPICAL VA	UNIT				
V_{DS}	Drain-to-Source Voltage 30						
Q_g	Gate Charge Total (4.5 V)	13		nC			
Q_{gd}	Gate Charge Gate-to-Drain	2.8	nC				
В	Drain-to-Source On-Resistance	V _{GS} = 4.5 V 4.8		mΩ			
R _{DS(on)}	Drain-to-Source On-Resistance	V _{GS} = 10 V	3.5	mΩ			
$V_{GS(th)}$	Threshold Voltage	1.4	V				

Ordering Information⁽¹⁾

Device	Qty	Media	Package	Ship
CSD17577Q5A	2500	13-Inch Reel	SON 5 × 6 mm	Tape and
CSD17577Q5AT	250	7-Inch Reel	Plastic Package	Reel

(1) For all available packages, see the orderable addendum at the end of the data sheet.

Absolute Maximum Ratings

T _A = 2	5°C	VALUE	UNIT
V_{DS}	Drain-to-Source Voltage	30	٧
V_{GS}	Gate-to-Source Voltage	±20	٧
	Continuous Drain Current (Package limited)	60	
I _D	Continuous Drain Current (Silicon limited), T _C = 25°C	83	Α
	Continuous Drain Current (1)	22	
I_{DM}	Pulsed Drain Current (2)	280	Α
п	Power Dissipation ⁽¹⁾	3	W
P _D	Power Dissipation, T _C = 25°C	53	VV
T _J , T _{stg}	Operating Junction and Storage Temperature Range	-55 to 150	ů
E _{AS}	Avalanche Energy, single pulse $I_D = 28$, $L = 0.1$ mH, $R_G = 25$ Ω	39	mJ

- (1) Typical $R_{\theta JA}=40^{\circ} C/W$ on a 1-inch 2 , 2-oz. Cu pad on a 0.06-inch thick FR4 PCB.
- (2) Max R_{θ,IC} = 2.8°C/W, pulse duration ≤100 μs, duty cycle ≤1%

Gate Charge

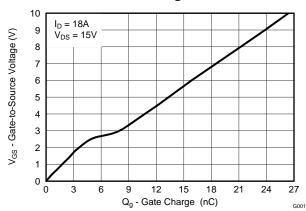






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4 Revision History

DATE	REVISION	NOTES
August 2014	*	Initial release.

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5 Specifications

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5.1 Electrical Characteristics

 $(T_{\Delta} = 25^{\circ}C \text{ unless otherwise stated})$

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
STATIC	CHARACTERISTICS					
BV _{DSS}	Drain-to-Source Voltage	V _{GS} = 0 V, I _D = 250 μA	30			V
I _{DSS}	Drain-to-Source Leakage Current	V _{GS} = 0 V, V _{DS} = 24 V			1	μΑ
I _{GSS}	Gate-to-Source Leakage Current	V _{DS} = 0 V, V _{GS} = 20 V			100	nA
V _{GS(th)}	Gate-to-Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1.1	1.4	1.8	V
В	Drain-to-Source On-Resistance	$V_{GS} = 4.5 \text{ V}, I_D = 10 \text{ A}$		4.8	5.8	mΩ
R _{DS(on)}	Drain-to-Source On-Resistance	$V_{GS} = 10 \text{ V}, I_D = 18 \text{ A}$		3.5	4.2	mΩ
g _{fs}	Transconductance	V _{DS} = 3 V, I _D = 18 A		79		S
DYNAMI	C CHARACTERISTICS					
C _{iss}	Input Capacitance		,	1780	2310	pF
C _{oss}	Output Capacitance	$V_{GS} = 0 \text{ V}, V_{DS} = 15 \text{ V}, f = 1 \text{ MHz}$		208	270	pF
C _{rss}	Reverse Transfer Capacitance			79	102	pF
R_G	Series Gate Resistance			1.4	2.8	Ω
Q_g	Gate Charge Total (4.5 V)			13	17	nC
Qg	Gate Charge Total (10 V)			27	35	nC
Q _{gd}	Gate Charge Gate-to-Drain	V _{DS} = 15 V, I _D = 18 A		2.8		nC
Q_{gs}	Gate Charge Gate-to-Source			5.1		nC
Q _{g(th)}	Gate Charge at V _{th}			2.5		nC
Q _{oss}	Output Charge	V _{DS} = 15 V, V _{GS} = 0 V		6		nC
t _{d(on)}	Turn On Delay Time			3		ns
t _r	Rise Time	V _{DS} = 15 V, V _{GS} = 10 V,		12		ns
t _{d(off)}	Turn Off Delay Time	$I_{DS} = 18 \text{ A}, R_G = 0 \Omega$		18		ns
t_f	Fall Time			2		ns
DIODE C	CHARACTERISTICS					
V_{SD}	Diode Forward Voltage	I _{SD} = 18 A, V _{GS} = 0 V		8.0	1	V
Q _{rr}	Reverse Recovery Charge	V _{DS} = 15 V, I _F = 18 A,		8.2		nC
t _{rr}	Reverse Recovery Time	di/dt = 300 A/µs		9.3		ns

5.2 Thermal Information

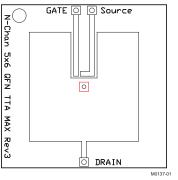
 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

	THERMAL METRIC	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction-to-Case Thermal Resistance ⁽¹⁾			2.8	°C/W
$R_{\theta JA}$	Junction-to-Ambient Thermal Resistance (1)(2)			50	C/VV

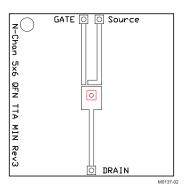
⁽¹⁾ R_{0JC} is determined with the device mounted on a 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu pad on a 1.5-inches × 1.5-inches (3.81-cm × 3.81-cm), 0.06-inch (1.52-mm) thick FR4 PCB. R_{0JC} is specified by design, whereas R_{0JA} is determined by the user's board design.

(2) Device mounted on FR4 material with 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu.

Product Folder Links: CSD17577Q5A



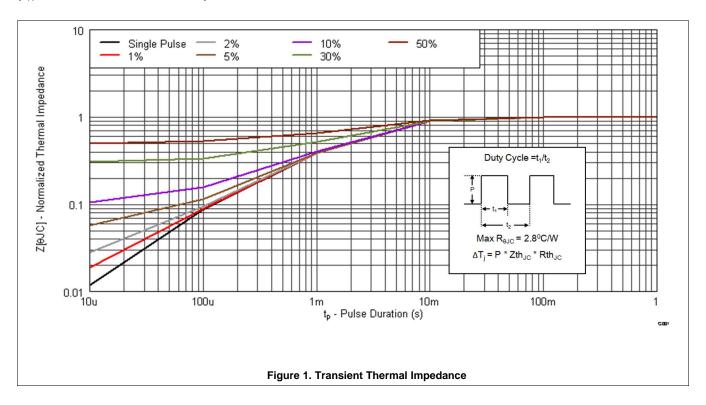
Max $R_{\theta JA} = 50^{\circ} C/W$ when mounted on 1 inch² (6.45 cm²) of 2-oz. (0.071-mm thick) Cu.



Max $R_{\theta JA} = 140^{\circ} C/W$ when mounted on a minimum pad area of 2-oz. (0.071-mm thick) Cu.

5.3 Typical MOSFET Characteristics

(T_A = 25°C unless otherwise stated)



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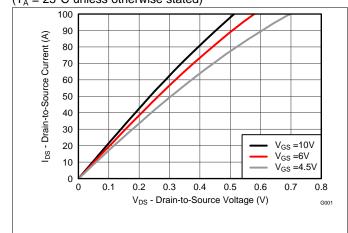
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Typical MOSFET Characteristics (continued)

(T_A = 25°C unless otherwise stated)



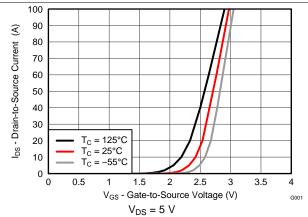
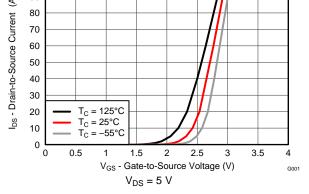


Figure 2. Saturation Characteristics



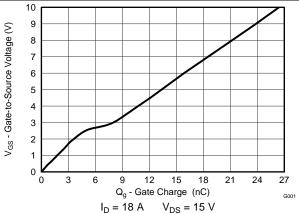


Figure 3. Transfer Characteristics

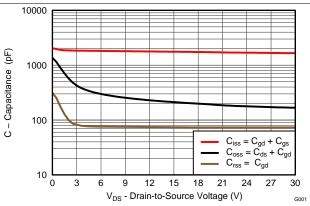


Figure 4. Gate Charge

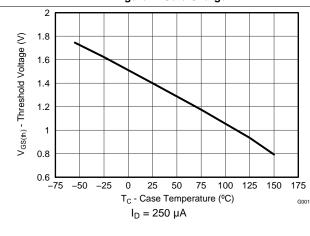


Figure 5. Capacitance

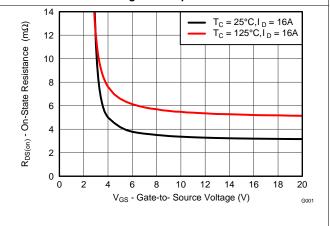


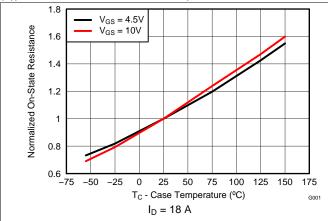
Figure 6. Threshold Voltage vs Temperature

Figure 7. On-State Resistance vs Gate-to-Source Voltage

TEXAS INSTRUMENTS

Typical MOSFET Characteristics (continued)

(T_A = 25°C unless otherwise stated)



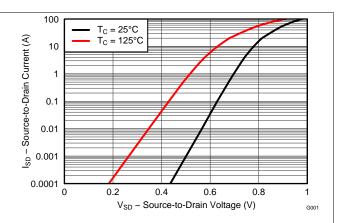
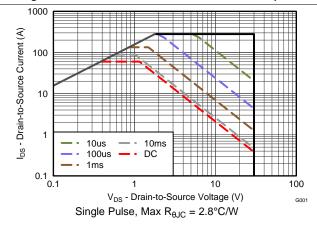


Figure 8. Normalized On-State Resistance vs Temperature





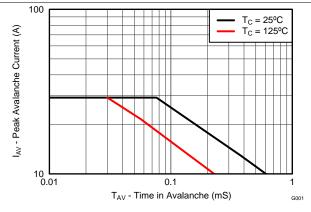


Figure 10. Maximum Safe Operating Area

Figure 11. Single Pulse Unclamped Inductive Switching

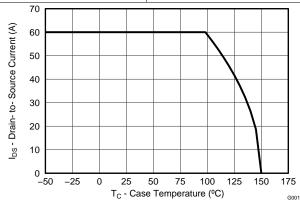


Figure 12. Maximum Drain Current vs Temperature

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6 Device and Documentation Support

6.1 Trademarks

NexFET is a trademark of Texas Instruments.

6.2 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

6.3 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

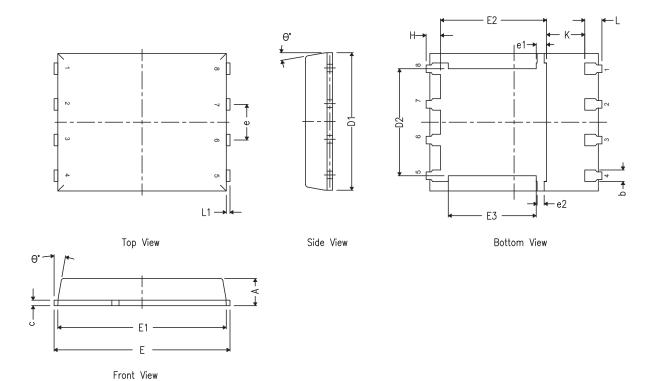
Product Folder Links: CSD17577Q5A



7 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

7.1 Q5A Package Dimensions

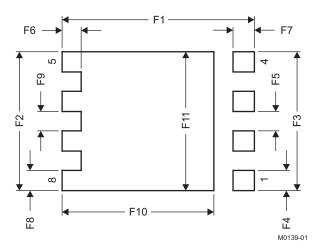


DIM	MILLIMETERS							
DIM	MIN	NOM	MAX					
Α	0.90	1.00	1.10					
b	0.33	0.41	0.51					
С	0.20	0.25	0.34					
D1	4.80	4.90	5.00					
D2	3.61	3.81	4.02					
E	5.90	6.00	6.10					
E1	5.70	5.75	5.80					
E2	3.38	3.58	3.78					
E3	3.03	3.13	3.23					
е	1.17	1.27	1.37					
e1	0.27	0.37	0.47					
e2	0.15	0.25	0.35					
Н	0.41	0.56	0.71					
K	1.10	_	_					
L	0.51	0.61	0.71					
L1	0.06	0.13	0.20					
θ	0°	_	12°					

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7.2 Recommended PCB Pattern

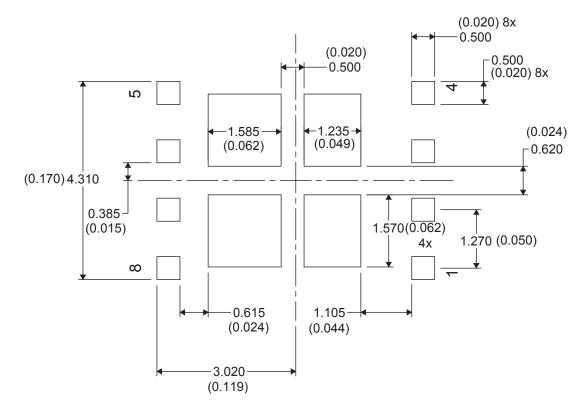


Recommended PCB Pattern (continued)

DIM	MILLIM	ETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
F1	6.205	6.305	0.244	0.248	
F2	4.46	4.56	0.176	0.18	
F3	4.46	4.56	0.176	0.18	
F4	0.65	0.7	0.026	0.028	
F5	0.62	0.67	0.024	0.026	
F6	0.63	0.68	0.025	0.027	
F7	0.7	0.8	0.028	0.031	
F8	0.65	0.7	0.026	0.028	
F9	0.62	0.67	0.024	0.026	
F10	4.9	5	0.193	0.197	
F11	4.46	4.56	0.176	0.18	

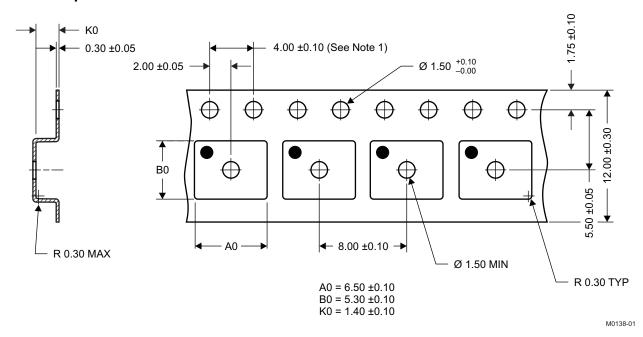
For recommended circuit layout for PCB designs, see application note SLPA005 – Reducing Ringing Through PCB Layout Techniques.

7.3 Recommended Stencil Opening



TEXAS INSTRUMENTS

7.4 Q5A Tape and Reel Information



Notes:

- 1. 10-sprocket hole-pitch cumulative tolerance ±0.2
- 2. Camber not to exceed 1 mm in 100 mm, noncumulative over 250 mm
- 3. Material: black static-dissipative polystyrene
- 4. All dimensions are in mm (unless otherwise specified).
- 5. A0 and B0 measured on a plane 0.3 mm above the bottom of the pocket.

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PACKAGE OPTION ADDENDUM

28-Aug-2014

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
CSD17577Q5A	ACTIVE	VSONP	DQJ	8	2500	Pb-Free (RoHS Exempt)	CU SN	Level-1-260C-UNLIM	-40 to 85	CSD17577	Samples
CSD17577Q5AT	ACTIVE	VSONP	DQJ	8	250	Pb-Free (RoHS Exempt)	CU SN	Level-1-260C-UNLIM	-40 to 85	CSD17577	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE OPTION ADDENDUM

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